Electronic Supplementary Material (ESI) for Journal of Materials Chemistry
This journal is © The Royal Society of Chemistry 2012

Electronic Supplementary Information for

Metalorganic chemical vapor deposition of aluminum oxynitride from dimethylaluminum hydride and oxygen: growth mode dependence and performance optimization

Gang He,[a*] Zhaoqi Sun,[a] Shiwei Shi,[a] Xiaoshuang Chen,[b] Jianguo Lv,[c] and Lide Zhang[d]

[a]*School of Physics and Materials Science, Anhui University, Hefei 230039, People's Republic of China.*

[b]*National Laboratory for Infrared Physics, Chinese Academy of Sciences, Shanghai Institute of Technical Physics, 500 Yutian Road, Shanghai 200083, People's Republic of China.*

[c]*Department of Physics and Electronic Engineering, Hefei Normal University, Hefei 230061,China;*

[d]*Key Laboratory of Materials Physics, Anhui Key Laboratory of Nanomaterials and Nanostructure, Institute of Solid State Physics, Chinese Academy of Sciences, Hefei 230031, People's Republic of China.*

Email: hegang@ahu.edu.cn

This journal is © The Royal Society of Chemistry 2012

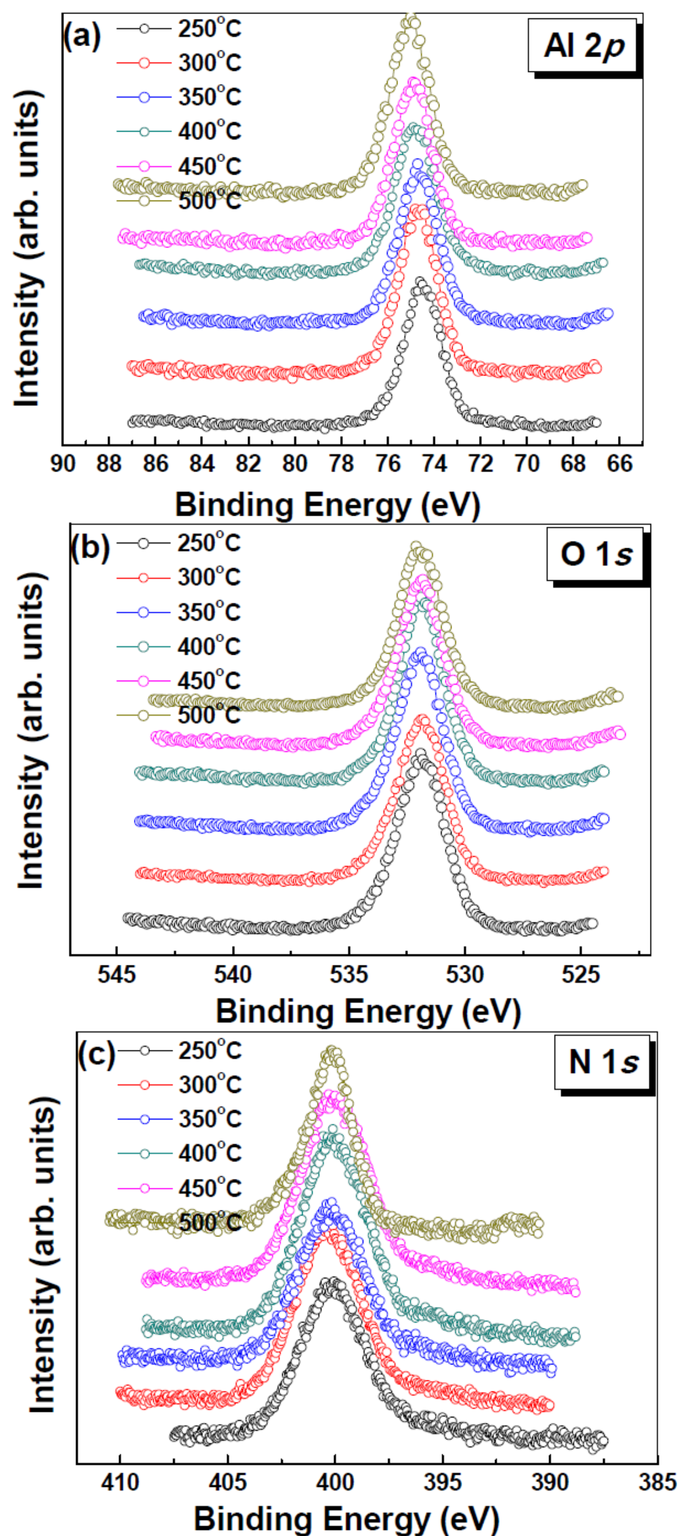

Fig. S1 Deposition temperature dependent Al 2*p*, O 1*s*, and N 1*s* core level

photoemission spectra of as-processed AlO_xN_y films grown on Si. All the samples were sputtered by Ar^+ for 1min.

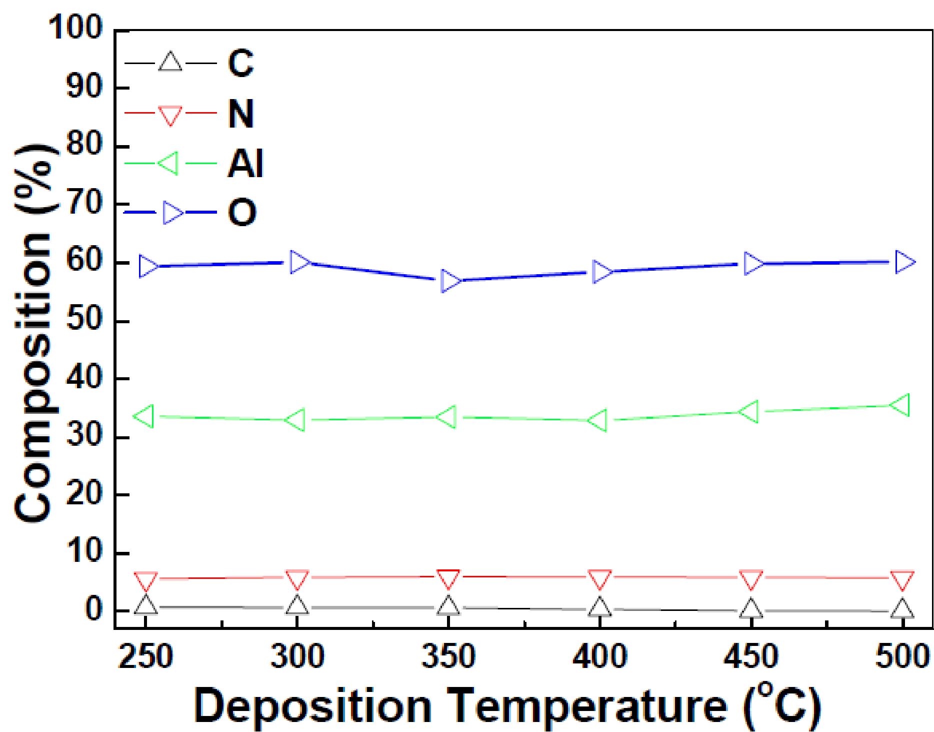

Fig. S2 Deposition temperature dependent composition distribution in as-processed AlO_xN_y films. All the samples were sputtered by Ar^+ for 1min.